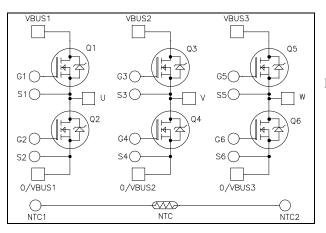
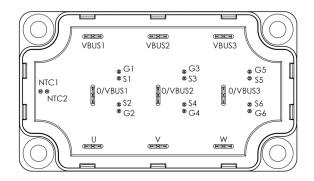


Triple phase leg Super Junction MOSFET Power Module





Absolute maximum ratings

Symbol Unit Parameter Max ratings Drain - Source Breakdown Voltage 900 V V_{DSS} $T_c = 25^{\circ}C$ 59 Continuous Drain Current I_D $T_c = 80^{\circ}C$ 44 А 150 I_{DN} Pulsed Drain current V Gate - Source Voltage ± 20 V_{GS} R_{DSon} Drain - Source ON Resistance 60 mΩ $T_c = 2\overline{5^{\circ}C}$ Maximum Power Dissipation 462 W PD I_{AR} Avalanche current (repetitive and non repetitive) 8.8 A 2.9 E_{AR} Repetitive Avalanche Energy mJ E_{AS} Single Pulse Avalanche Energy 1940

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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$V_{DSS} = 900V$

 $R_{DSon} = 60m\Omega \max @ Tj = 25^{\circ}C$ $I_{D} = 59A @ Tc = 25^{\circ}C$

Application

- Welding converters
 - Switched Mode Power Supplies
 - Uninterruptible Power Supplies
- Motor control

Power Semiconducto

- Ultra low R_{DSon}
- Low Miller capacitance
- Ultra low gate charge
- Avalanche energy rated
- Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Very low (12mm) profile
- Each leg can be easily paralleled to achieve a phase leg of three times the current capability
- Module can be configured as a three phase bridge
- Module can be configured as a boost followed by a full bridge
- RoHS Compliant

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All ratings (a) $T_i = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics Symbol **Characteristic Test Conditions** Min Тур Max Unit $V_{GS} = 0V, V_{DS} = 900V$ $T_i = 25^{\circ}C$ 200 Zero Gate Voltage Drain Current μA $I_{DSS} \\$ $V_{GS} = 0V, V_{DS} = 900V$ 1000 $T_i = 125^{\circ}C$ $R_{DS(on)}$ Drain – Source on Resistance $V_{GS} = 10V, I_D = 52A$ 50 60 mΩ Gate Threshold Voltage $V_{GS} = V_{DS}, I_D = 6mA$ 2.5 3 3.5 V V_{GS(th)} $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ Gate - Source Leakage Current 200 I_{GSS} nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
C _{iss}	Input Capacitance	$V_{GS} = 0V$; $V_{DS} = 100V$		13.6		nF
C _{oss}	Output Capacitance	f = 1 MHz		0.66		III
Qg	Total gate Charge	$V_{GS} = 10V$		540		
Q_{gs}	Gate – Source Charge	$V_{Bus} = 400 V$		64		nC
Q_{gd}	Gate – Drain Charge	$I_D = 52A$		230		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (125°C)		70		
Tr	Rise Time	$V_{GS} = 10V$		20		ns
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 600V$ $I_D = 52A$ $R_G = 3.8\Omega$		400		
$T_{\rm f}$	Fall Time			25		
Eon	Turn-on Switching Energy	Inductive switching @ 25°C		3		. т
$\mathrm{E}_{\mathrm{off}}$	Turn-off Switching Energy	$V_{GS} = 10V$; $V_{Bus} = 600V$ $I_D = 52A$; $R_G = 3.8\Omega$		1.5		mJ
Eon	Turn-on Switching Energy	Inductive switching @ 125°C		4.2		т
E _{off}	Turn-off Switching Energy	$V_{GS} = 10V$; $V_{Bus} = 600V$ $I_D = 52A$; $R_G = 3.8\Omega$		1.7		mJ

Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
т	Continuous Source current		$Tc = 25^{\circ}C$			59	٨
I_S	(Body diode)		$Tc = 80^{\circ}C$			44	А
V _{SD}	Diode Forward Voltage	$V_{GS} = 0V, I_S = -52A$			0.8	1.2	V
t _{rr}	Reverse Recovery Time	$I_s = -52A$	$T_j = 25^{\circ}C$		920		ns
Qn	Reverse Recovery Charge	$V_{\rm R} = 400 V$ $di_{\rm S}/dt = 200 {\rm A}/\mu {\rm s}$	$T_j = 25^{\circ}C$		60		μC



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Thermal and package characteristics

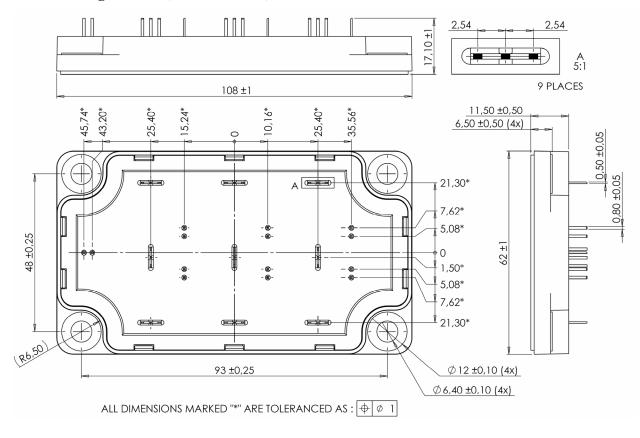
Symbol	Characteristic		Min	Тур	Max	Unit	
R _{thJC}	Junction to Case Thermal Resistance					0.27	°C/W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T _J	Operating junction temperature range			-40		150	
T _{STG}	Storage Temperature Range			-40		125	°C
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
Wt	Package Weight					250	g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
B _{25/85}	$T_{25} = 298.15 \text{ K}$			3952		Κ
$\Delta B/B$		$T_C=100^{\circ}C$		4		%

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature
R_T: Thermistor value at T

SP6-P Package outline (dimensions in mm)

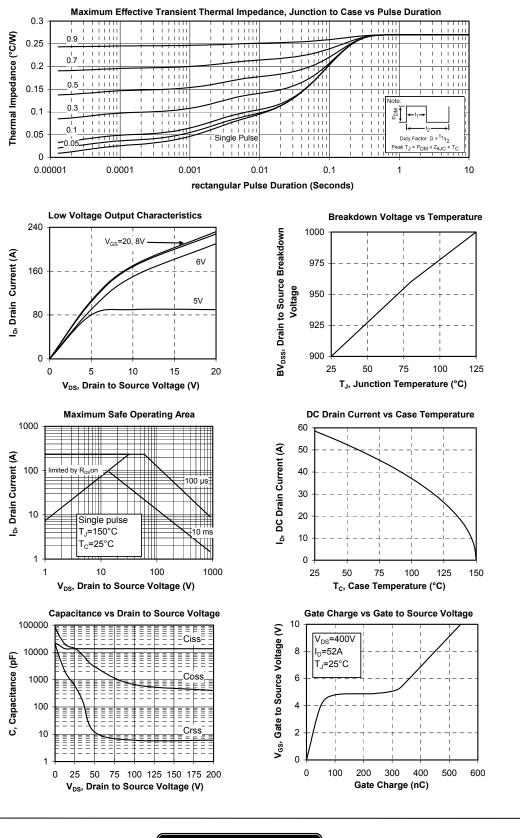


See application note 1902 - Mounting Instructions for SP6-P (12mm) Power Modules on www.microsemi.com



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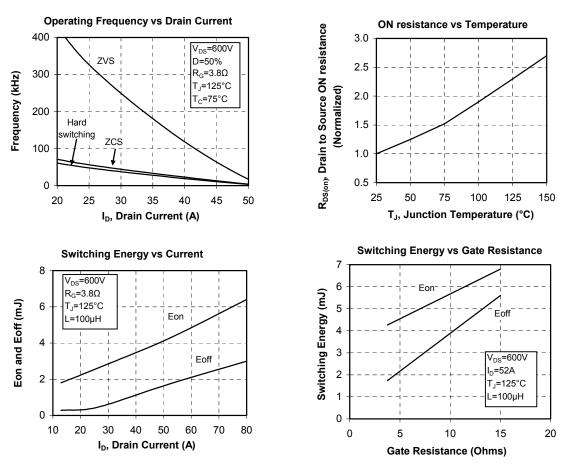
Typical Performance Curve



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